

MITSUBISHI IGBT MODULES
CM200E3U-24F

HIGH POWER SWITCHING USE

CM200E3U-24F



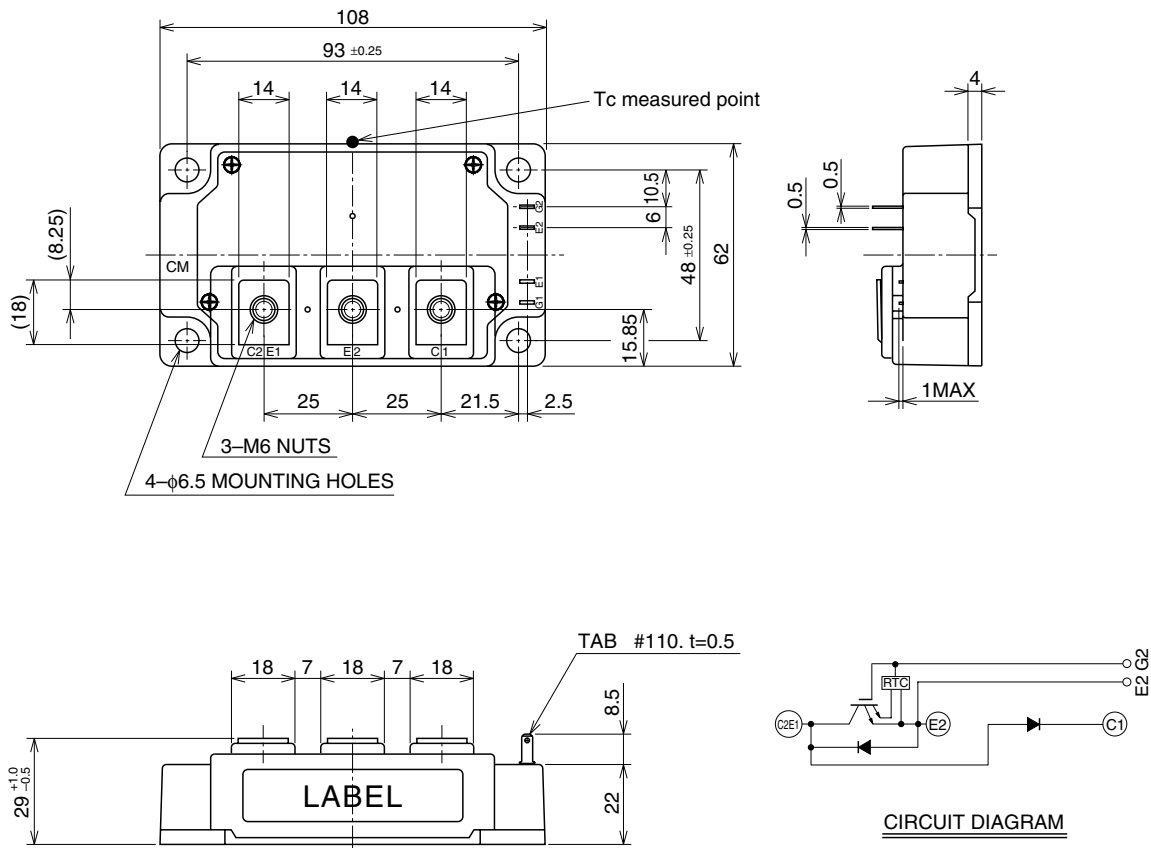
- IC200A
- VCES 1200V
- Insulated Type
- 1-element in a pack

APPLICATION

Brake

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



MAXIMUM RATINGS (T_j = 25°C)

| Symbol | Parameter | Conditions | Ratings | Unit | |
|--------------------------|---------------------------------|--|---------------------------|-------|---|
| V _{CE} S | Collector-emitter voltage | G-E Short | 1200 | V | |
| V _{GE} S | Gate-emitter voltage | C-E Short | ±20 | V | |
| I _C | Collector current | T _C = 25°C | 200 | A | |
| I _{CM} | | Pulse (Note 2) | 400 | | |
| I _E (Note 1) | Emitter current | T _C = 25°C | 200 | A | |
| I _{EM} (Note 1) | | Pulse (Note 2) | 400 | | |
| P _C (Note 3) | Maximum collector dissipation | T _C = 25°C | 830 | W | |
| V _{RRM} | Repetitive peak reverse voltage | Clamp diode part | 1200 | V | |
| I _F | Forward current | T _C = 25°C | Clamp diode part | 200 | A |
| I _{FM} | | Pulse | Clamp diode part (Note 2) | 400 | |
| T _j | Junction temperature | | -40 ~ +150 | °C | |
| T _{stg} | Storage temperature | | -40 ~ +125 | °C | |
| V _{iso} | Isolation voltage | Main terminal to base plate, AC 1 min. | 2500 | V | |
| — | Torque strength | Main Terminal M6 | 3.5 ~ 4.5 | N • m | |
| — | | Mounting holes M6 | 3.5 ~ 4.5 | N • m | |
| — | Weight | Typical value | 400 | g | |

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

| Symbol | Parameter | Test conditions | Limits | | | Unit |
|--------------------------|--------------------------------------|--|--|------|---------|------|
| | | | Min. | Typ. | Max. | |
| I _{CE} S | Collector cutoff current | V _{CE} = V _{CE} S, V _{GE} = 0V | — | — | 1 | mA |
| V _{GE(th)} | Gate-emitter threshold voltage | I _C = 20mA, V _{CE} = 10V | 5 | 6 | 7 | V |
| I _{GE} S | Gate leakage current | V _{GE} = V _{CE} S, V _{CE} = 0V | — | — | 40 | μA |
| V _{CE(sat)} | Collector-emitter saturation voltage | T _j = 25°C | — | 1.8 | 2.4 | V |
| | | T _j = 125°C | I _C = 200A, V _{GE} = 15V | — | 1.9 | |
| C _{ies} | Input capacitance | V _{CE} = 10V V _{GE} = 0V | — | — | 78 | nF |
| C _{oes} | Output capacitance | | — | — | 3.4 | |
| C _{res} | Reverse transfer capacitance | | — | — | 2.0 | |
| Q _G | Total gate charge | V _{CC} = 600V, I _C = 200A, V _{GE} = 15V | — | 2200 | — | nC |
| t _{d(on)} | Turn-on delay time | V _{CC} = 600V, I _C = 200A V _{GE1} = V _{GE2} = 15V R _G = 1.6Ω, Inductive load switching operation | — | — | 300 | ns |
| t _r | Turn-on rise time | | — | — | 80 | |
| t _{d(off)} | Turn-off delay time | | — | — | 500 | |
| t _f | Turn-off fall time | | — | — | 300 | |
| t _{rr} (Note 1) | Reverse recovery time | I _E = 200A | — | — | 200 | ns |
| Q _{rr} (Note 1) | Reverse recovery charge | | — | 12.2 | — | μC |
| V _{EC} (Note 1) | Emitter-collector voltage | I _E = 200A, V _{GE} = 0V | — | — | 3.2 | V |
| R _G | External gate resistance | | 1.6 | — | 16 | Ω |
| R _{th(j-c)Q} | Thermal resistance*1 | IGBT part | — | — | 0.15 | °C/W |
| R _{th(j-c)R} | | FWDi part | — | — | 0.18 | |
| R _{th(j-c)Q} | Thermal resistance | T _c measured point is just under the chips | — | — | 0.091*3 | °C/W |
| V _{FM} | Forward voltage drop | I _F = 200A, Clamp diode part | — | — | 3.2 | V |
| t _{rr} | Reverse recovery time | I _F = 200A V _{CC} = 600V, V _{GE1} = V _{GE2} = 15V R _G = 1.6Ω, Inductive load switching operation, Clamp diode part | — | — | 200 | ns |
| Q _{rr} | Reverse recovery charge | | — | 12.2 | — | μC |
| R _{th(j-c)R} | Thermal resistance*1 | Clamp diode part | — | — | 0.18 | °C/W |
| R _{th(c-f)} | Contact thermal resistance | Case to fin, Thermal compound applied*2 (1/2 module) | — | 0.04 | — | |

Note 1. I_E, V_{EC}, t_{rr}, Q_{rr}, die/dt represent characteristics of the anti-parallel, emitter to collector free-wheel diode (FWDi).

2. Pulse width and repetition rate should be such that the device junction temp. (T_j) does not exceed T_{jmax} rating.

3. Junction temperature (T_j) should not increase beyond 150°C.

4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

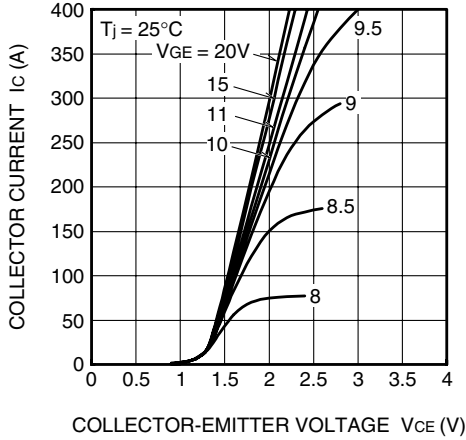
*1 : T_c measured point is indicated in OUTLINE DRAWING.

*2 : Typical value is measured by using Shin-etsu Silicone "G-746".

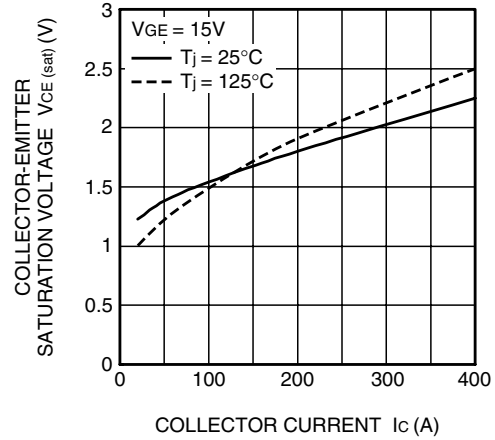
*3 : If you use this value, R_{th(f-a)} should be measured just under the chips.

PERFORMANCE CURVES

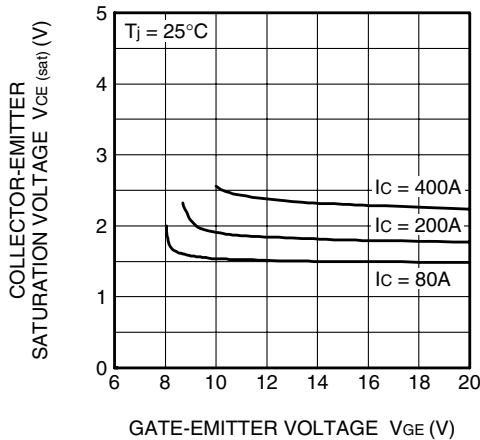
OUTPUT CHARACTERISTICS (TYPICAL)



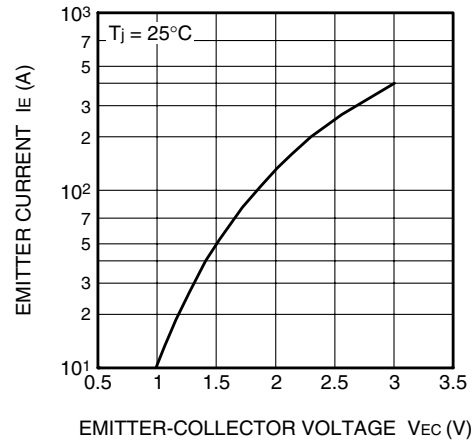
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



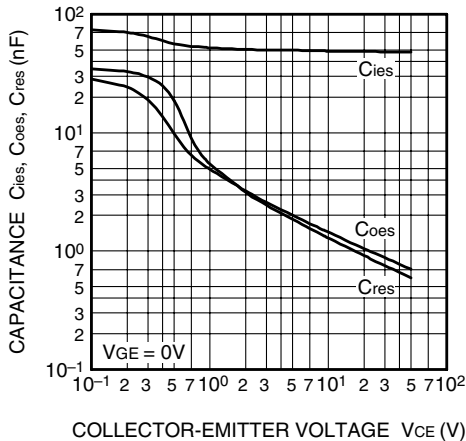
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



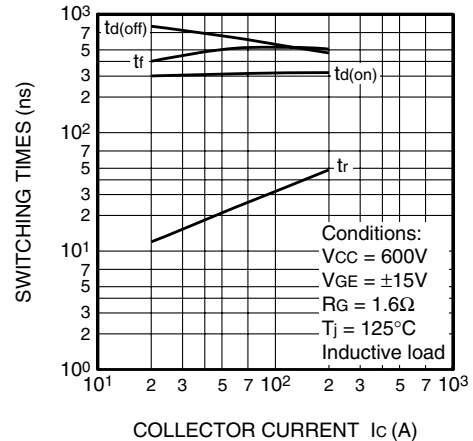
FREE-WHEEL DIODE AND CLAMP DIODE FORWARD CHARACTERISTICS (TYPICAL)



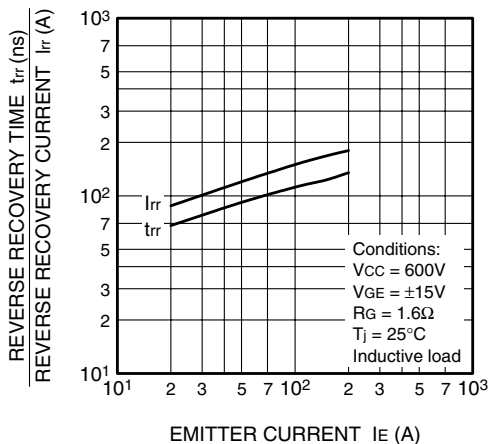
CAPACITANCE-VCE CHARACTERISTICS (TYPICAL)



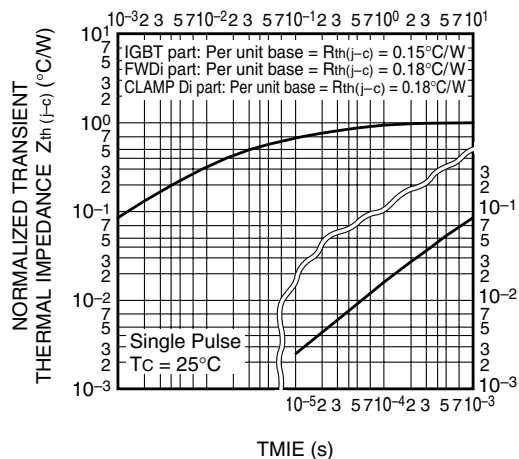
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)



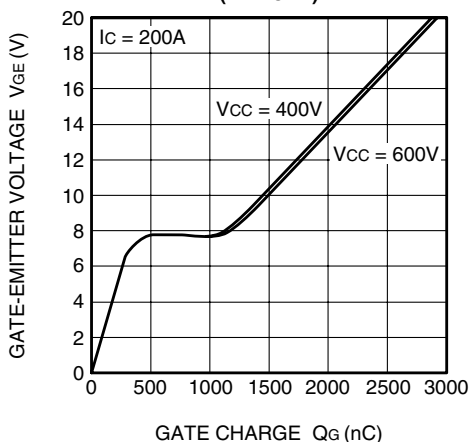
REVERSE RECOVERY CHARACTERISTICS OF CLAMP DIODE (TYPICAL)



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (IGBT part & FWDi part & CLAMP DIODE part)



GATE CHARGE CHARACTERISTICS (TYPICAL)





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